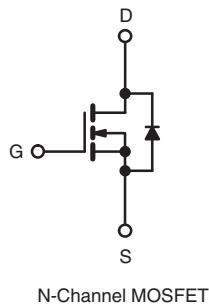


D Series Power MOSFET

PRODUCT SUMMARY	
V_{DS} (V) at T_J max.	650
$R_{DS(on)}$ max. at 25 °C (Ω)	$V_{GS} = 10$ V 0.340
Q_g (Max.) (nC)	90
Q_{gs} (nC)	14
Q_{gd} (nC)	22
Configuration	Single



ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	SiHP17N60D-E3
Lead (Pb)-free and Halogen-free	SiHP17N60D-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 30	
Continuous Drain Current ($T_J = 150$ °C)	V_{GS} at 10 V	17	A
		10.7	
	I_{DM}	48	
Pulsed Drain Current ^a		2.22	W/°C
Linear Derating Factor		165.6	mJ
Single Pulse Avalanche Energy ^b	E_{AS}	277.8	W
Maximum Power Dissipation	P_D	- 55 to + 150	°C
Operating Junction and Storage Temperature Range	T_J, T_{stg}	24	V/ns
Drain-Source Voltage Slope	$T_J = 125$ °C	0.2	
Reverse Diode dV/dt ^d		300	°C
Soldering Recommendations (Peak Temperature) ^c	for 10 s		

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature.
- b. $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 2.3$ mH, $R_g = 25$ Ω, $I_{AS} = 12$ A.
- c. 1.6 mm from case.
- d. $I_{SD} \leq I_D$, starting $T_J = 25$ °C.

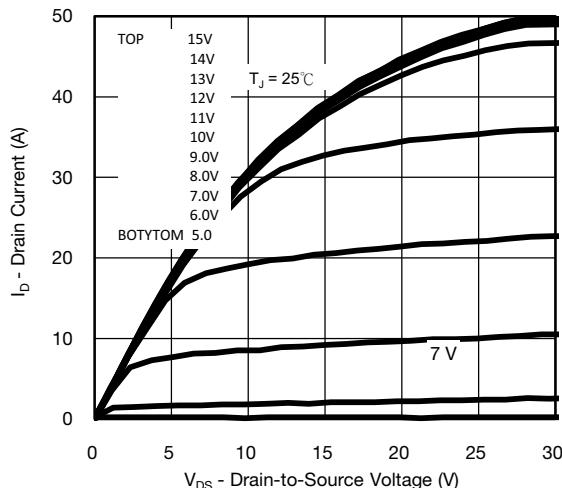
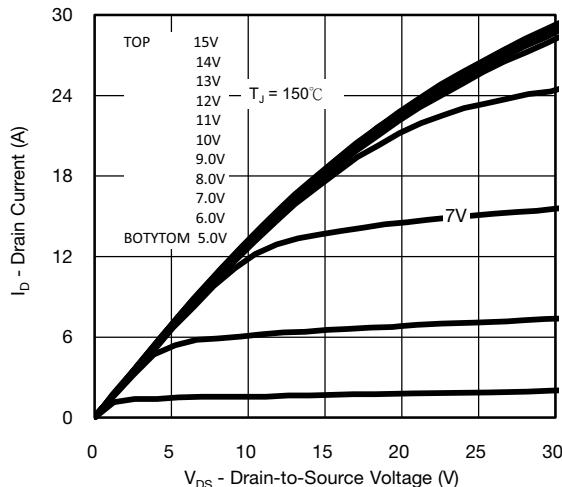
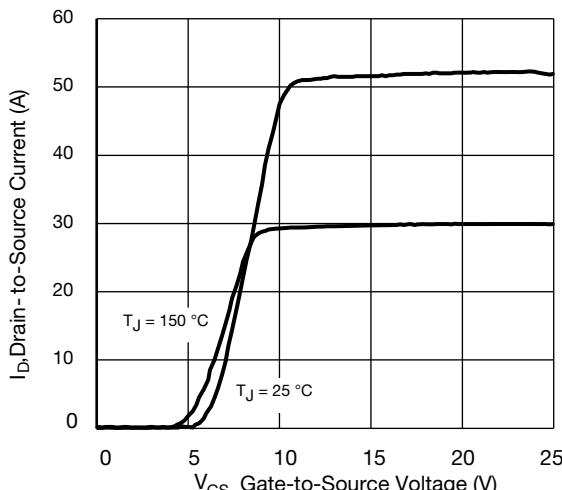
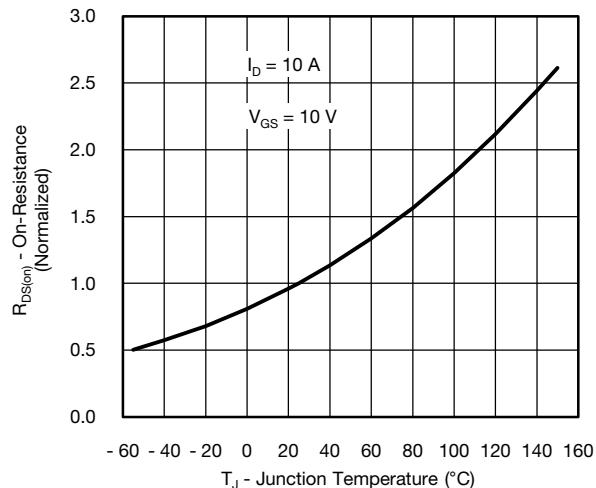
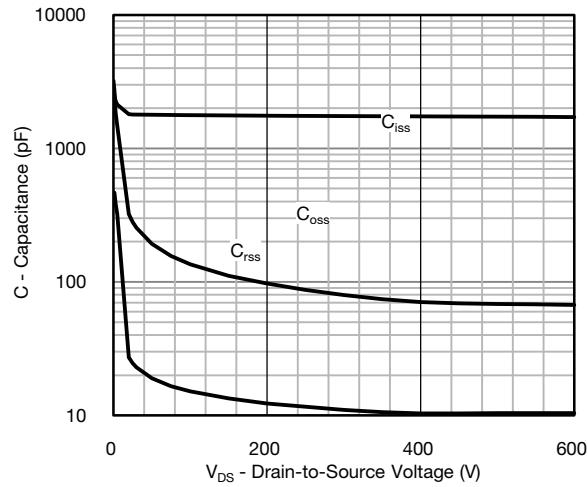
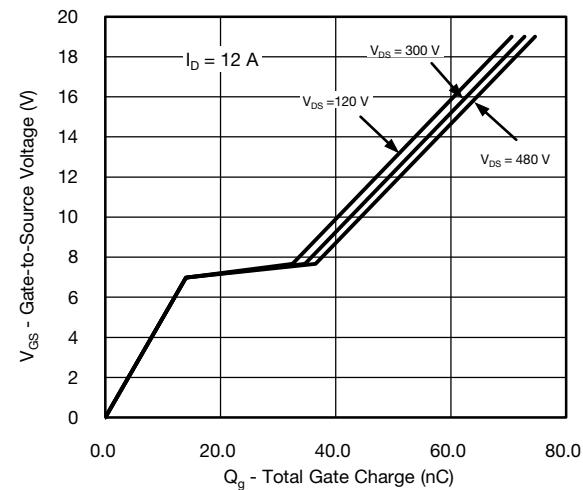


THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.45	

SPECIFICATIONS ($T_J = 25^\circ\text{C}$, unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$		600	-	-	V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25°C , $I_D = 1 \text{ mA}$		-	0.7	-	$^\circ\text{C}/\text{V}$	
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$		3	-	5	V	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30 \text{ V}$		-	-	± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600 \text{ V}$, $V_{GS} = 0 \text{ V}$		-	-	1	μA	
		$V_{DS} = 480 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 125^\circ\text{C}$		-	-	100		
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$	$I_D = 8 \text{ A}$	-	0.275	0.340	Ω	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 50 \text{ V}$, $I_D = 8 \text{ A}$		-	6.2	-	S	
Dynamic								
Input Capacitance	C_{iss}	$V_{GS} = 0 \text{ V}$, $V_{DS} = 100 \text{ V}$, $f = 1 \text{ MHz}$		-	1780	-	pF	
Output Capacitance	C_{oss}			-	140	-		
Reverse Transfer Capacitance	C_{rss}			-	15	-		
Total Gate Charge	Q_g	$V_{GS} = 10 \text{ V}$	$I_D = 8 \text{ A}$, $V_{DS} = 480 \text{ V}$	-	45	90	nC	
Gate-Source Charge	Q_{gs}			-	14	-		
Gate-Drain Charge	Q_{gd}			-	22	-		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 300 \text{ V}$, $I_D = 8 \text{ A}$ $R_g = 9.1 \Omega$, $V_{GS} = 10 \text{ V}$		-	22	45	ns	
Rise Time	t_r			-	56	85		
Turn-Off Delay Time	$t_{d(off)}$			-	37	75		
Fall Time	t_f			-	30	60		
Internal Gate Resistance	R_g	$f = 1 \text{ MHz}$, open drain		-	1.6	-	Ω	
Drain-Source Body Diode Characteristics								
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	17	A	
Pulsed Diode Forward Current	I_{SM}			-	-	48		
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}$, $I_S = 8 \text{ A}$, $V_{GS} = 0 \text{ V}$		-	-	1.5	V	
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25^\circ\text{C}$, $I_F = I_S$, $dl/dt = 100 \text{ A}/\mu\text{s}$, $V_R = 20 \text{ V}$		-	633	950	ns	
Body Diode Reverse Recovery Charge	Q_{rr}			-	7	15	μC	
Reverse Recovery Current	I_{RRM}			-	21	42	A	

Note

a. Repetitive rating; pulse width limited by maximum junction temperature.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics, $T_c = 150\text{ }^\circ\text{C}$

Fig. 2 - Typical Output Characteristics, $T_c = 150\text{ }^\circ\text{C}$

Fig. 3 - Typical Transfer Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

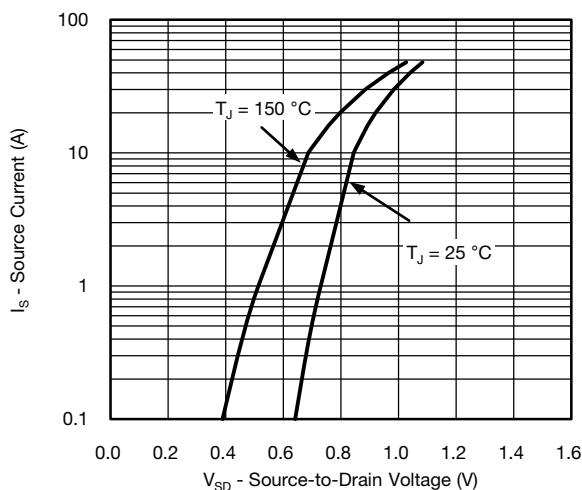


Fig. 7 - Typical Source-Drain Diode Forward Voltage

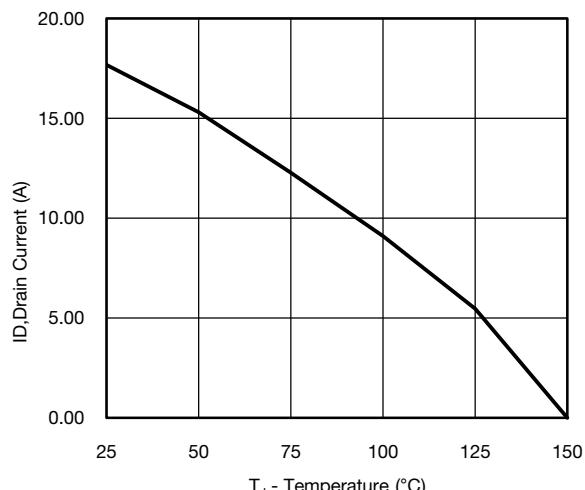


Fig. 9 - Maximum Drain Current vs. Case Temperature

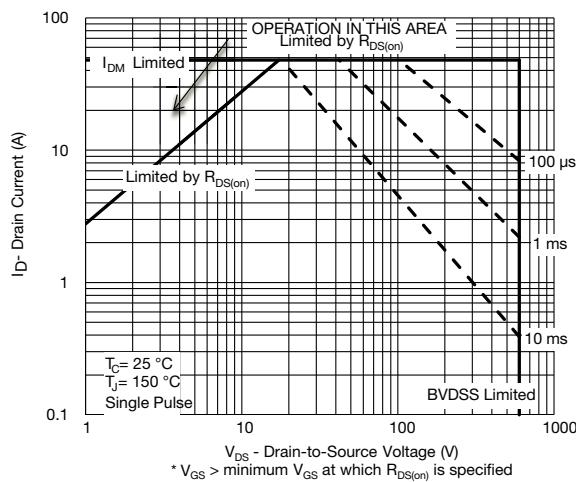


Fig. 8 - Maximum Safe Operating Area

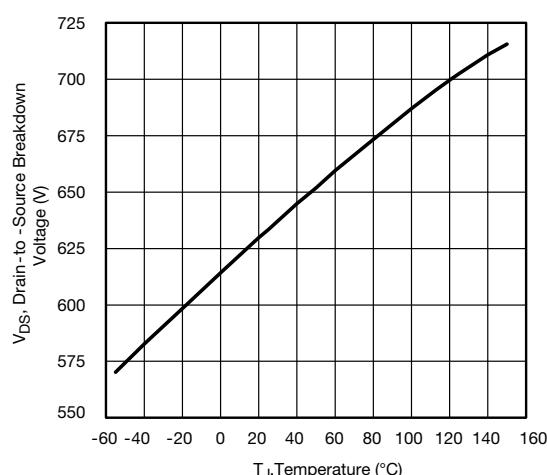


Fig. 10 - Typical Drain-to-Source Voltage vs. Temperature

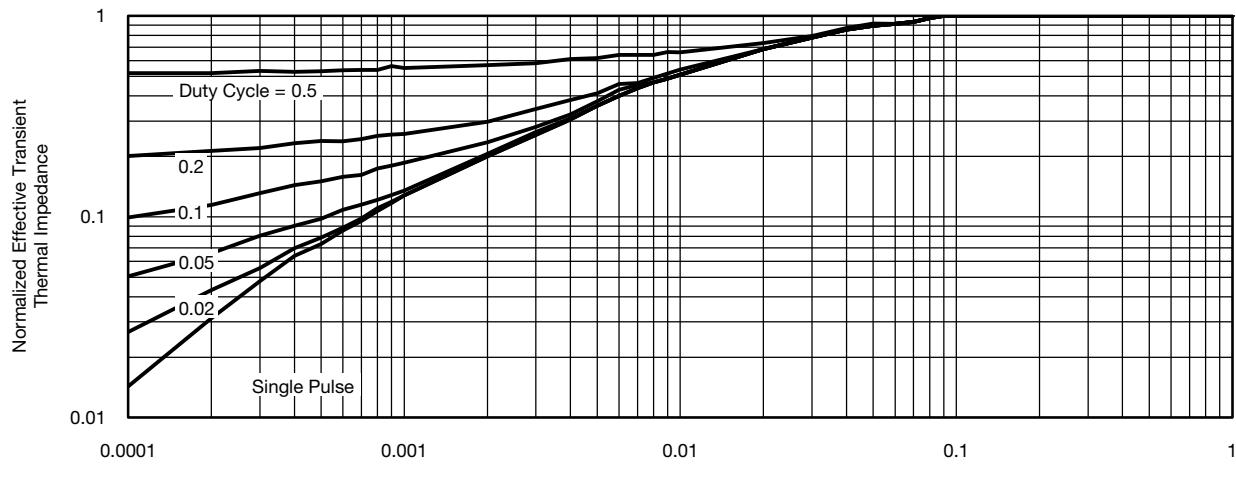
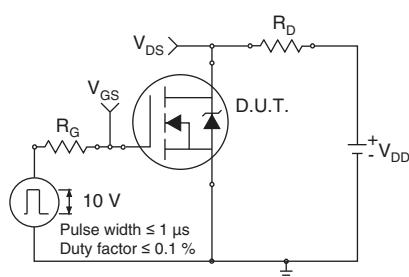
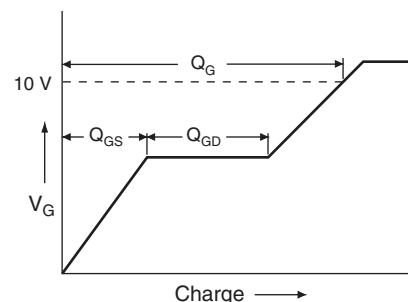
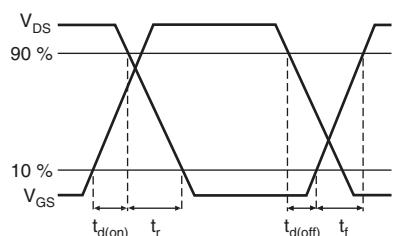
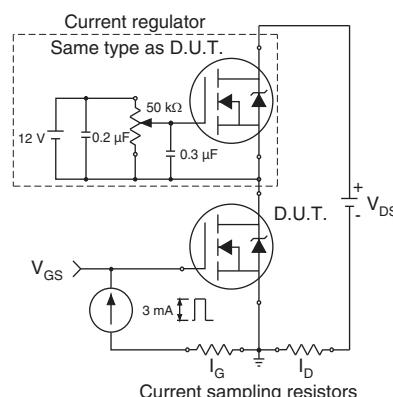
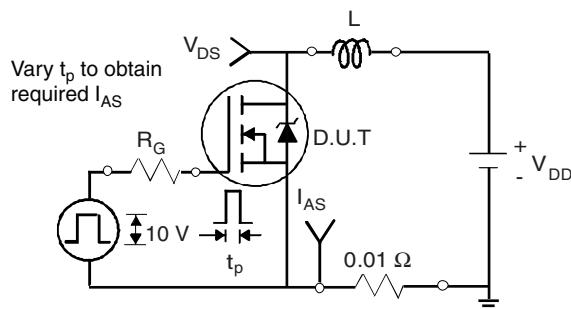
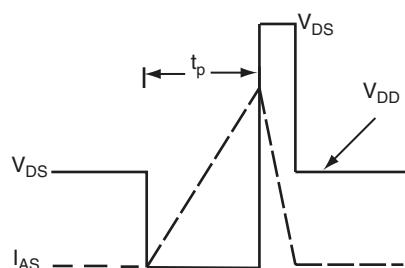
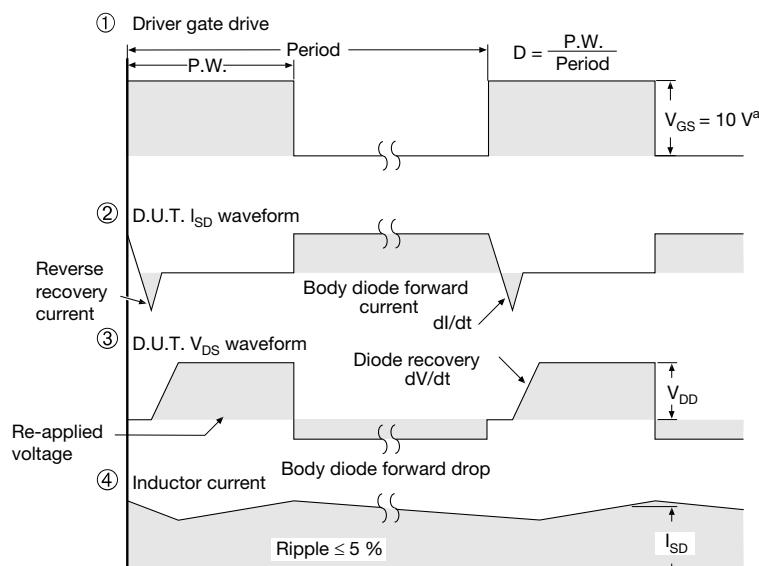
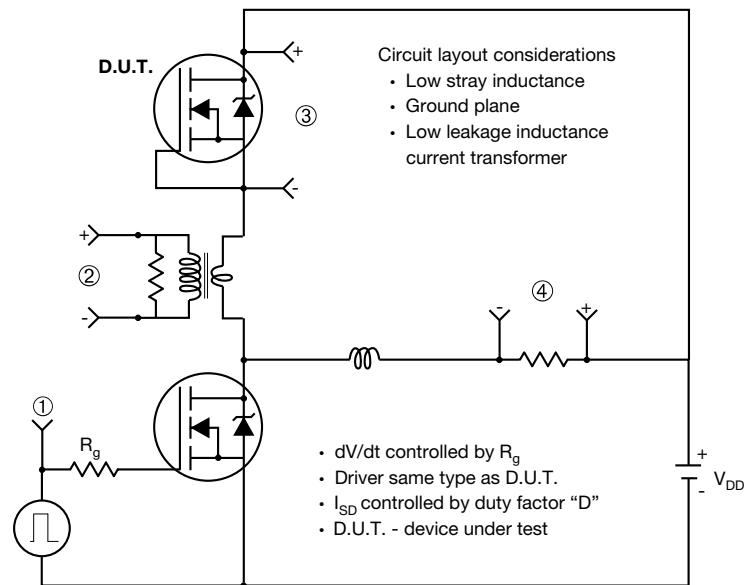


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case


Fig. 12 - Switching Time Test Circuit

Fig. 16 - Basic Gate Charge Waveform

Fig. 13 - Switching Time Waveforms

Fig. 17 - Gate Charge Test Circuit

Fig. 14 - Unclamped Inductive Test Circuit

Fig. 15 - Unclamped Inductive Waveforms

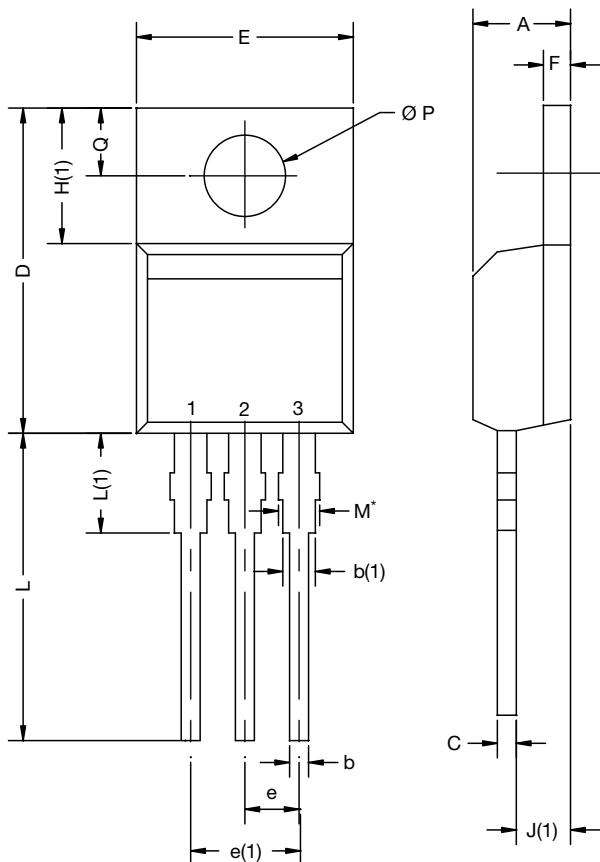
Peak Diode Recovery dV/dt Test Circuit

Note

a. $V_{GS} = 5 \text{ V}$ for logic level devices

Fig. 18 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91464.

TO-220-1



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
Ø P	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: X15-0364-Rev. C, 14-Dec-15
DWG: 6031

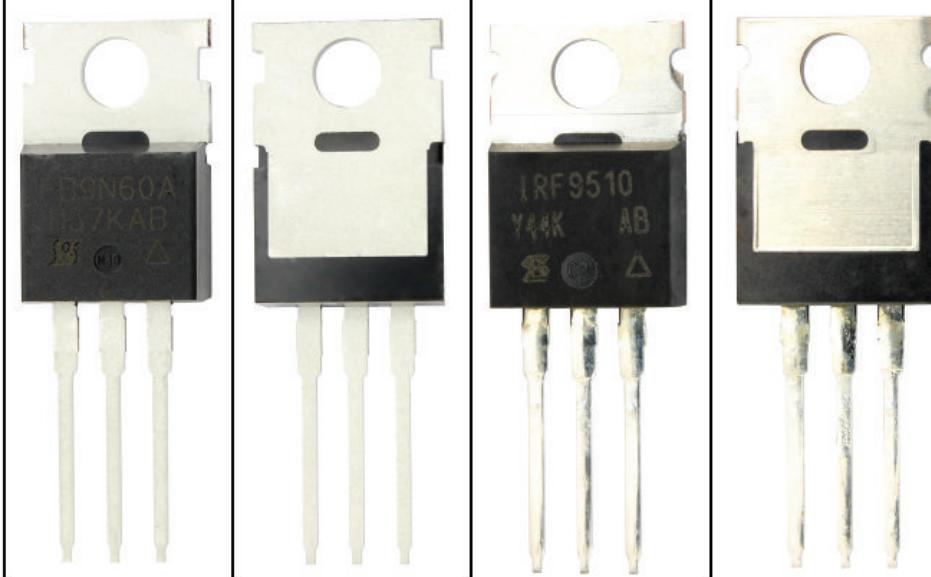
Note

- $M^* = 0.052$ inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM

Package Picture

ASE

Xi'an



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.